

**SANYO**

No.3103A

**2SA1624**

PNP Epitaxial Planar Silicon Transistor

Color TV Chroma Output,  
High-Voltage Driver Applications**Features**

- High breakdown voltage
- Small reverse transfer capacitance and excellent high frequency characteristics
- Adoption of FBET process

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	-300	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-300	V
Emitter to Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-100	mA
Peak Collector Current	i <sub>cp</sub>	-200	mA
Collector Dissipation	P <sub>C</sub>	500	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

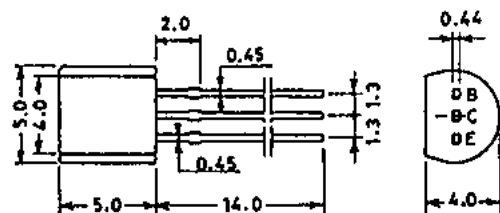
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = -200V, I <sub>E</sub> = 0			-0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V, I <sub>C</sub> = 0			-0.1	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1mA	60		320	
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -30V, I <sub>C</sub> = -10mA		70		MHz
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA			-0.6	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA			-1.0	V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0	-300			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -1mA, R <sub>BE</sub> = ∞	-300			V
E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -10μA, I <sub>C</sub> = ∞	-5			V
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -30V, f = 1MHz		2.4		pF
Reverse Transfer Capacitance	C <sub>ro</sub>	V <sub>CB</sub> = -30V, f = 1MHz		1.5		pF

※ : The 2SA1624 is classified by 1mA h<sub>FE</sub> as follows :

60	D	120	100	E	200	160	F	320
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Case Outline 2003A  
(unit : mm)



JEDEC: TO-92  
EIAJ : SC-43  
SANYO: NP

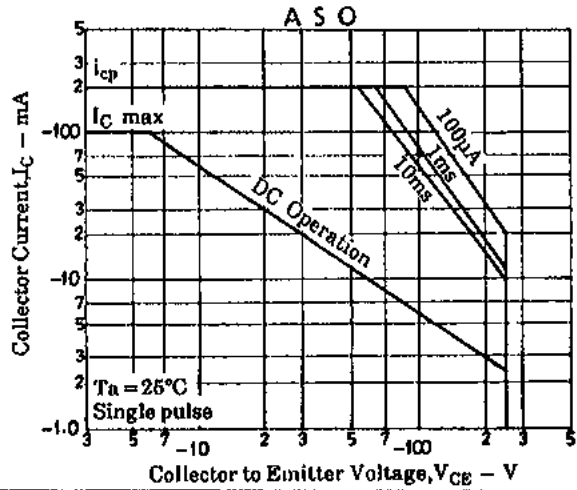
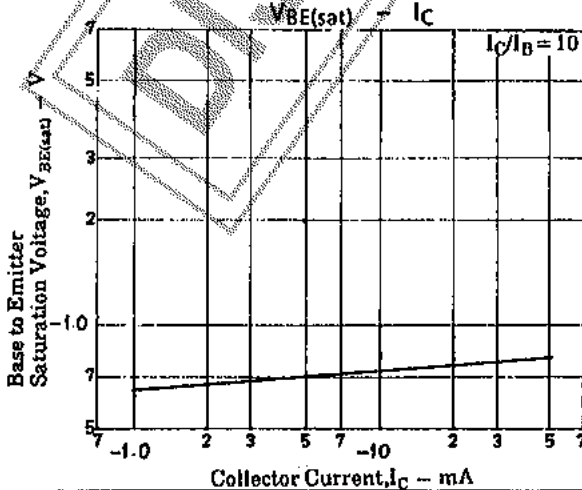
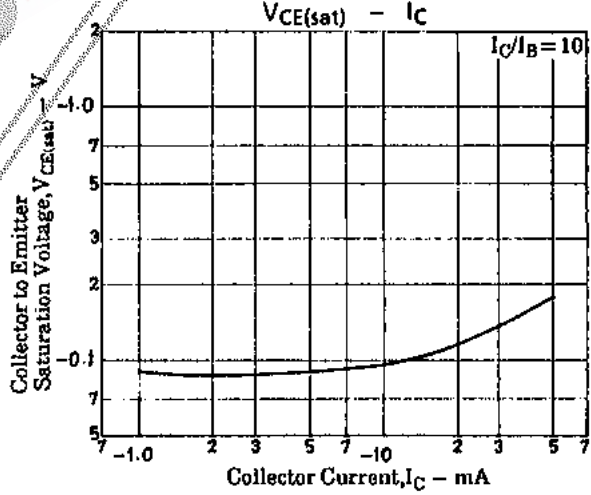
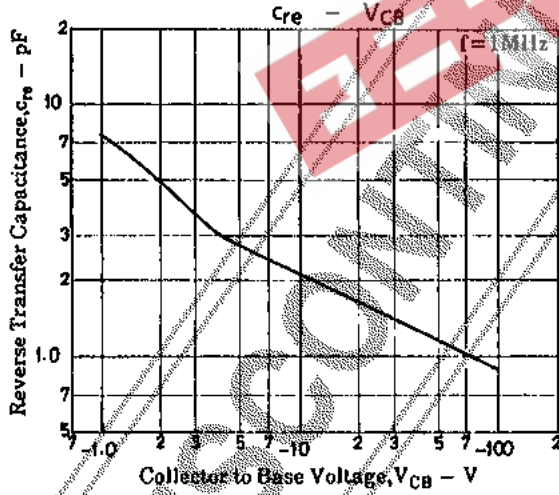
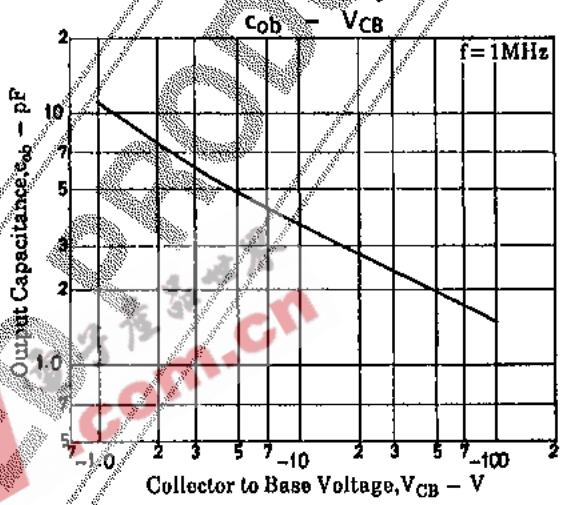
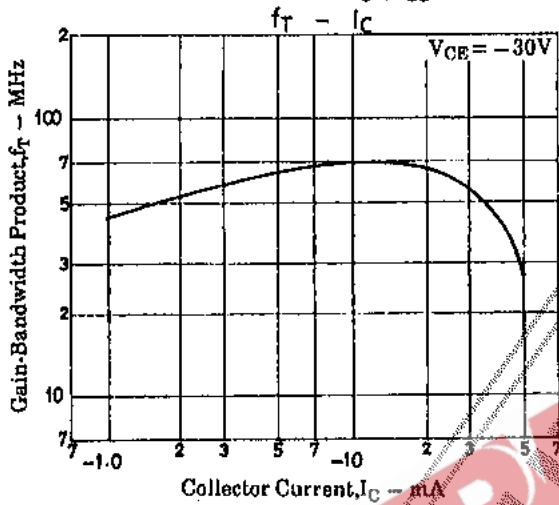
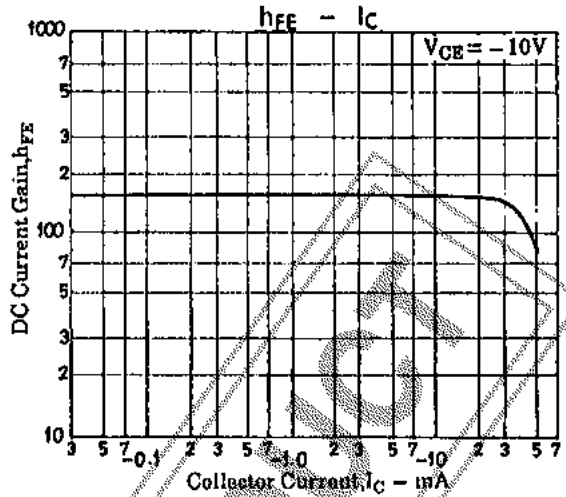
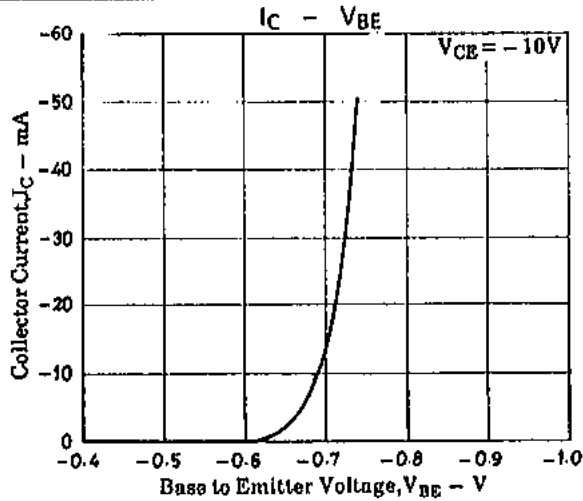
B: Base  
C: Collector  
E: Emitter

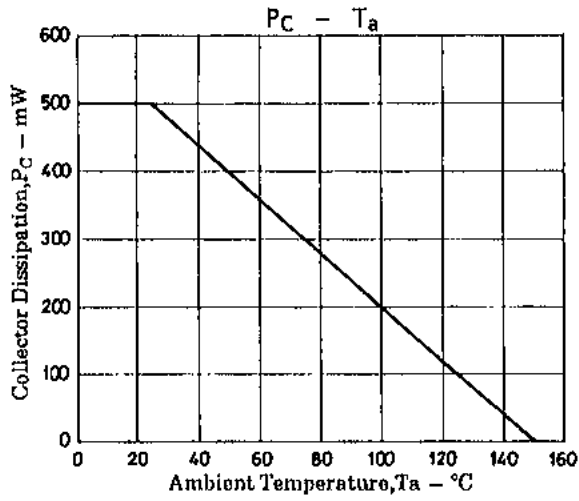
Specifications and information herein are subject to change without notice.

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2SA1624





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